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Team Nexperia



BC847BS

45 V, 100 mA NPN/NPN general-purpose transistor Rev. 03 — 18 February 2009 Produ

Product data sheet

1. Product profile

1.1 General description

NPN/NPN general-purpose transistor pair in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

PNP/PNP complement: BC857BS.

1.2 Features

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- No mutual interference between the transistors

1.3 Applications

■ General-purpose switching and amplification

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|---------------------------|--|-----|-----|-----|------|
| Per trans | istor | | | | | |
| V_{CEO} | collector-emitter voltage | open base | - | - | 45 | V |
| I _C | collector current | | - | - | 100 | mA |
| h _{FE} | DC current gain | $V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$ | 200 | - | 450 | |



45 V, 100 mA NPN/NPN general-purpose transistor

2. Pinning information

Table 2. Pinning

| | 9 | | |
|-----|---------------|--------------------|----------------|
| Pin | Description | Simplified outline | Graphic symbol |
| 1 | emitter TR1 | D- D- D. | |
| 2 | base TR1 | <u> </u> | 6 5 4 |
| 3 | collector TR2 | | TR2 |
| 4 | emitter TR2 | 0 | (TR1) |
| 5 | base TR2 | □1 □2 □3 | |
| 6 | collector TR1 | | 1 2 3 |
| | | | sym020 |

3. Ordering information

Table 3. Ordering information

| Type number | Package | Package | | | | |
|-------------|---------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| BC847BS | SC-88 | plastic surface-mounted package; 6 leads | SOT363 | | | |

4. Marking

Table 4. Marking codes

| Type number | Marking code ^[1] |
|-------------|-----------------------------|
| BC847BS | 1F* |

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

BC847BS NXP Semiconductors

45 V, 100 mA NPN/NPN general-purpose transistor

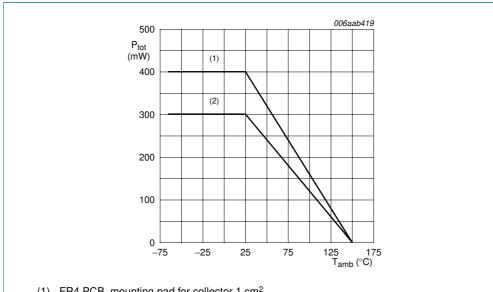
Limiting values 5.

Table 5. **Limiting values** In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------------|---|-------|------|------|
| Per transis | stor | | | | |
| V_{CBO} | collector-base voltage | open emitter | - | 50 | V |
| V_{CEO} | collector-emitter voltage | open base | - | 45 | V |
| V_{EBO} | emitter-base voltage | open collector | - | 5 | V |
| I _C | collector current | | - | 100 | mA |
| I _{CM} | peak collector current | single pulse; $t_p \le 1 \text{ ms}$ | - | 200 | mA |
| I _{BM} | peak base current | single pulse; $t_p \le 1 \text{ ms}$ | - | 200 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] - | 220 | mW |
| | | | [2] - | 250 | mW |
| Per device | | | | | |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] - | 300 | mW |
| | | | [2] - | 400 | mW |
| Tj | junction temperature | | - | 150 | °C |
| T _{amb} | ambient temperature | | -65 | +150 | °C |
| T _{stg} | storage temperature | | -65 | +150 | °C |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².



⁽¹⁾ FR4 PCB, mounting pad for collector 1 cm²

Fig 1. Per device: Power derating curves SOT363 (SC-88)

⁽²⁾ FR4 PCB, standard footprint

45 V, 100 mA NPN/NPN general-purpose transistor

6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|--|-------------|--------------|-----|-----|------|
| Per transis | stor | | | | | |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | | <u>[1]</u> _ | - | 568 | K/W |
| | | | [2] _ | - | 500 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | - | - | 230 | K/W |
| Per device | | | | | | |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | [1] - | - | 416 | K/W |
| | | | [2] _ | - | 313 | K/W |
| | | | | | | |

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

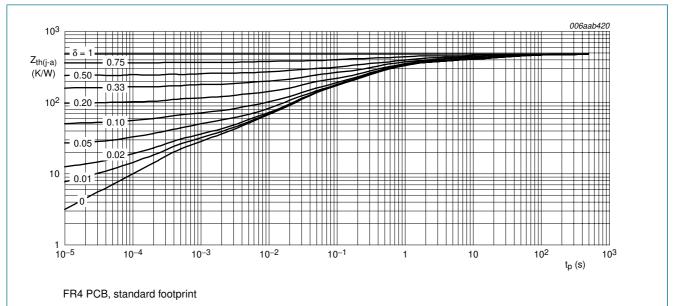
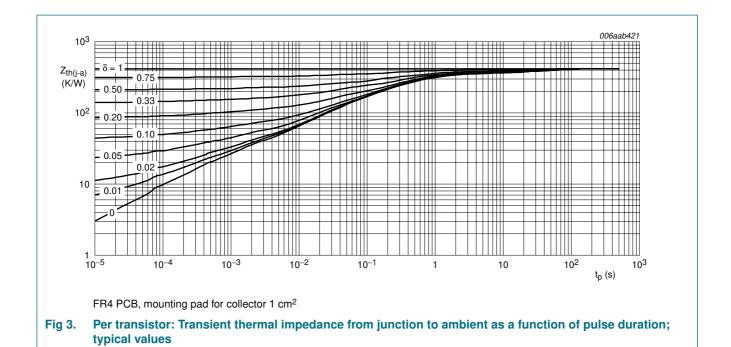


Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

45 V, 100 mA NPN/NPN general-purpose transistor



7. Characteristics

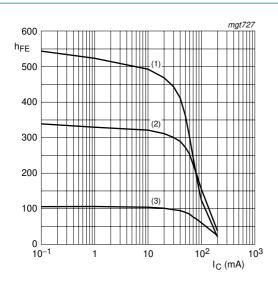
Table 7. Characteristics

T_{amb} = 25 °C unless otherwise specified.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------------------------|---|---|--------------|-----|-----|------|
| Per trans | sistor | | | | | |
| I_{CBO} | collector-base cut-off | $V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}$ | - | - | 15 | nA |
| | current | $V_{CB} = 30 \text{ V; } I_E = 0 \text{ A;}$ $T_j = 150 ^{\circ}\text{C}$ | - | - | 5 | μΑ |
| I _{EBO} | emitter-base cut-off current | $V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$ | - | - | 100 | nA |
| h _{FE} | DC current gain | $V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$ | 200 | - | 450 | |
| V _{CEsat} collector-emitter | $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$ | - | - | 100 | mV | |
| | saturation voltage | $I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$ | <u>[1]</u> - | - | 300 | mV |
| V_{BEsat} | base-emitter saturation voltage | $I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$ | - | 755 | - | mV |
| V_{BE} | base-emitter voltage | $I_C = 2 \text{ mA}$; $V_{CE} = 5 \text{ V}$ | 580 | 655 | 700 | mV |
| C _c | collector capacitance | $I_E = i_e = 0 A; V_{CB} = 10 V;$ f = 1 MHz | - | - | 1.5 | pF |
| C _e | emitter capacitance | $I_C = I_c = 0 A; V_{EB} = 0.5 V;$ f = 1 MHz | - | 11 | - | pF |
| f _T | transition frequency | $I_{C} = 10 \text{ mA}; V_{CE} = 5 \text{ V};$ f = 100 MHz | 100 | - | - | MHz |

^[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

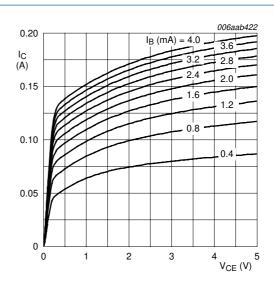
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$$V_{CE} = 5 V$$

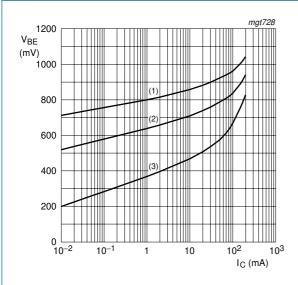
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \,^{\circ}C$

Fig 4. Per transistor: DC current gain as a function of collector current; typical values



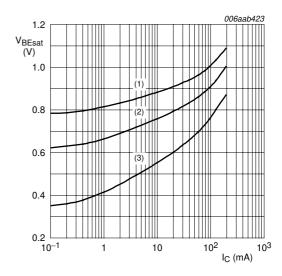
 $T_{amb} = 25 \, ^{\circ}C$

Fig 5. Per transistor: Collector current as a function of collector-emitter voltage; typical values



- $V_{CE} = 5 V$
- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 150 \, ^{\circ}C$

Fig 6. Per transistor: Base-emitter voltage as a function of collector current; typical values



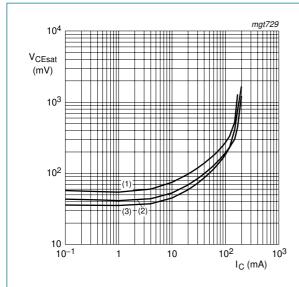
$$I_C/I_B = 20$$

- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 150 \, ^{\circ}C$

Fig 7. Per transistor: Base-emitter saturation voltage as a function of collector current; typical values

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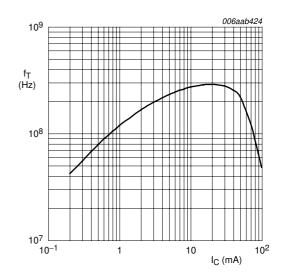
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 $I_{\rm C}/I_{\rm B} = 20$

- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \,^{\circ}C$

Fig 8. Per transistor: Collector-emitter saturation voltage as a function of collector current; typical values

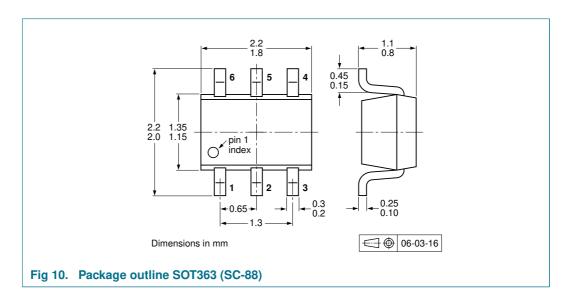


 V_{CE} = 5 V; f = 1 MHz; T_{amb} = 25 $^{\circ}C$

Fig 9. Per transistor: Transition frequency as a function of collector current; typical values

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8. Package outline



9. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

| Type number | Package | Description | | Packing quantity | |
|-------------|---------|------------------------------------|-----|------------------|-------|
| | | | | 3000 | 10000 |
| BC847BS | SOT363 | 4 mm pitch, 8 mm tape and reel; T1 | [2] | -115 | -135 |
| | | 4 mm pitch, 8 mm tape and reel; T2 | [3] | -125 | -165 |

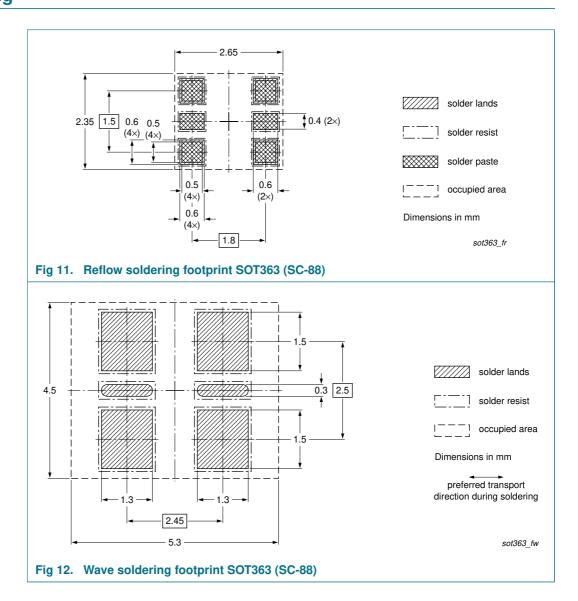
^[1] For further information and the availability of packing methods, see Section 13.

[2] T1: normal taping

[3] T2: reverse taping

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10. Soldering



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11. Revision history

Table 9. Revision history

| les | ce Supersedes | Change notic | Data sheet status | Release date | Document ID |
|------------------|---------------------------|---|--|--|-------------|
| 5_2 | BC847BS_2 | - | Product data sheet | 20090218 | BC847BS_3 |
| ntity guidelines | oly with the new identity | The format of this data sheet has been redesigned to comply with the new ident of NXP Semiconductors. | | | |
| | where appropriate. | Legal texts have | | | |
| | | | | | |
| | | | | | |
| | | | | | |
| | | | "Soldering": added | Section 10 "So | |
| | | d | "Legal information": update | Section 12 "Le | |
| _1 | BC847BS_1 | - | Product specification | 19990428 | BC847BS_2 |
| | - | - | Product specification | 19970714 | BC847BS_1 |
| | | l d - | "Legal information": update Product specification | Section 4 "Mar Section 7 "Cha Section 9 "Pac Section 10 "So Section 12 "Le 19990428 | |

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12. Legal information

12.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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